

Switch-mode Power Rectifiers MBR735, MBR745

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- Pb-Free Packages are Available*

Applications

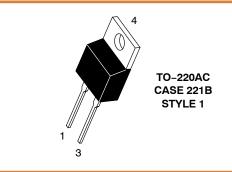
- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B

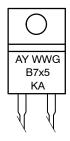
Machine Model C

SCHOTTKY BARRIER **RECTIFIERS** 7.5 AMPERES 35 and 45 VOLTS





MARKINGDIAGRAM



= Assembly Location

= Year WW = Work Week = Device Code B7x5 = 3 or 4

KΑ = Diode A Polarity = Pb-Free Package

See detailed ordering, marking and shipping information in the package dimensions section on page 4 of this data sheet.

NOTE: Some of the devices on this data sheet have been DISCONTINUED. Please refer to the table on page 4.

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V _{RRM} V _{RWM} V _R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR735 MBR745	35 45	V
I _{F(AV)}	Average Rectified Forward Current (T _C = 164°C) Per Device	7.5	А
I _{FRM}	Peak Repetitive Forward Current, (Square Wave, 20 kHz, T _C = 168°C)	7.5	A
I _{FSM}	Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	150	А
I _{RRM}	Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	1.0	A
T _{stg}	Storage Temperature Range	-65 to +175	°C
TJ	Operating Junction Temperature (Note 1)	-65 to +175	°C
dv/dt	Voltage Rate of Change (Rated V _R)	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Value	Unit
$R_{ heta JC}$	Maximum Thermal Resistance, Junction-to-Case	3.0	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction-to-Ambient	60	°C/W

ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Min	Тур	Max	Unit
VF	Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 7.5 \text{ Amps}, T_J = 125^{\circ}\text{C}$) ($i_F = 15 \text{ Amps}, T_J = 125^{\circ}\text{C}$) ($i_F = 15 \text{ Amps}, T_J = 25^{\circ}\text{C}$)	- - -	0.48 0.61 0.68	0.57 0.72 0.84	٧
i _R	Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	-	10 0.03	15 0.1	mA

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

^{1.} The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

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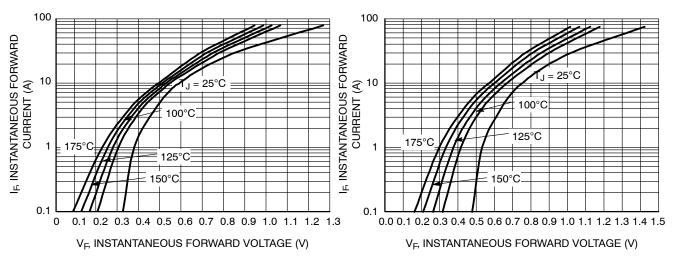


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

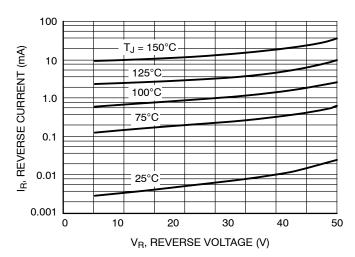


Figure 3. Typical Reverse Current

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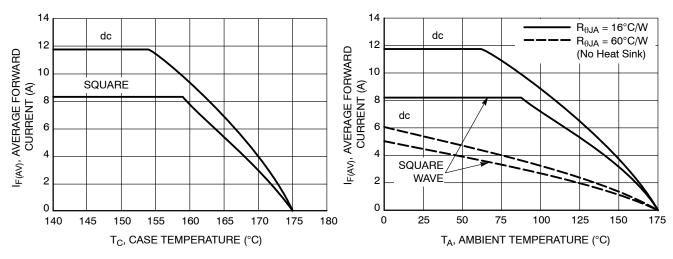


Figure 4. Current Derating, Case, Per Leg

Figure 5. Current Derating, Ambient, Per Leg

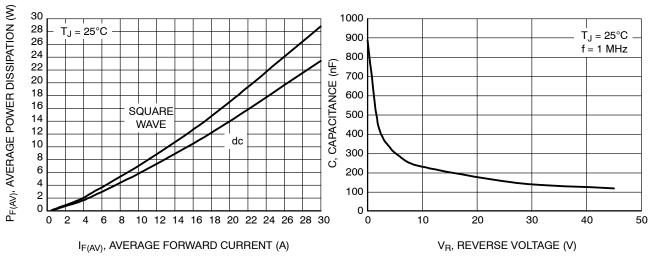


Figure 6. Forward Power Dissipation

Figure 7. Typical Capacitance

DEVICE ORDERING INFORMATION

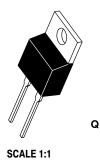
Device	Package	Shipping
MBR745G	TO-220 (Pb-Free)	50 Units/Rail

DISCONTINUED (Note 3)

MBR735	TO-220	50 Units/Rail	
MBR735G	TO-220 (Pb-Free)	50 Units/Rail	
MBR745	TO-220	50 Units/Rail	

^{3.} **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.





TO-220, 2-LEAD CASE 221B-04 ISSUE F

DATE 12 APR 2013

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.039	0.64	1.00
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

STYLE 1: PIN 1. CATHODE 2. N/A 3. ANODE

STYLE 2: PIN 1. ANODE 2. N/A 3. CATHODE 4. ANODE

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